

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Application of: William G. America

Conf. No.: 3775

Serial No.: 10/709,776

Art Unit: 2811

Filed: 5/27/2004

Dkt. #: FIS920040083US1 (IBMF-0058)

Title: SEMICONDUCTOR DEVICE FORMED
BY IN-SITU MODIFICATION OF
DIELECTRIC LAYER AND RELATED
METHODS

Examiner: Im, Junghwa M

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

AMENDMENT

Sir:

I. INTRODUCTORY COMMENTS

This paper is being filed in response to the Office Action dated November 30, 2006.

Please amend the above-referenced patent application as follows: